

AMENDMENTS TO THE CLAIMS

1. **(Currently amended)** A resin for a photoresist composition comprising a $-CR^1R^2OH$ group only at a terminal of a principal chain of the resin; (a1) a structural unit derived from a (meth)acrylate ester having an acid dissociable, dissolution inhibiting group; and (a2) a structural unit derived from a (meth)acrylate ester having a lactone ring, wherein R^1 and R^2 each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R^1 and R^2 is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups.
2. **(Canceled).**
3. **(Original)** A resin for a photoresist composition according to claim 1, wherein said electron attractive group is a fluorine atom or a fluorinated alkyl group.
4. **(Canceled)**
5. **(Canceled)**
6. **(Canceled)**
7. **(Canceled)**
8. **(Canceled)**
9. **(Currently amended)** A resin for a photoresist composition according to claim ~~8~~ 1, further comprising (a3) a structural unit derived from a (meth)acrylate ester having a hydroxyl group.
10. **(Previously presented)** A resin for a photoresist composition according to claim 1, with a weight average molecular weight of no more than 12,000.

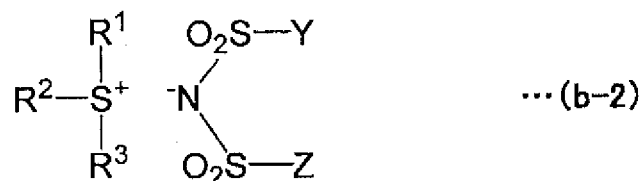
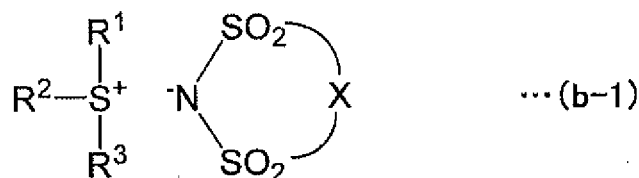
11. **(Previously presented)** A photoresist composition, comprising a resin for a photoresist composition according to claim 1.

12. **(Currently amended)** A photoresist composition according to claim 11, further comprising:

a resin comprising a $-\text{CR}^1\text{R}^2\text{OH}$ group only at a terminal of a principal chain of the resin, wherein R^1 and R^2 each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R^1 and R^2 is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups; and an acid generator as a component (B).

13. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

14. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), a sulfonium compound represented by either of general formulas (b-1) and (b-2) shown below:



wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; R^1 to R^3 each represent, independently, an aryl group or an alkyl group, and at least one of R^1 to R^3 is an aryl group.

15. **(Original)** A photoresist composition according to claim 14, further comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

16. **(Currently amended)** A photoresist composition according to claim 11, further comprising:

a resin comprising a $-CR^1R^2OH$ group only at a terminal of a principal chain of the resin, , wherein R^1 and R^2 each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R^1 and R^2 is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups;
and
a nitrogen-containing organic compound.

17. **(Currently amended)** A method for forming a resist pattern, ~~using a photoresist composition according to claim 11,~~ comprising the steps of:

applying a photoresist composition that comprises a resin comprising a $-CR^1R^2OH$ group only at a terminal of a principal chain of the resin, , wherein R^1 and R^2 each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R^1 and R^2 is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups to a surface of a substrate;
performing selective exposure through a desired mask pattern; and
performing developing to form a resist pattern.

18. **(Canceled)**

19. **(Canceled)**

20. **(Canceled)**

21. **(Canceled)**

Appl. No. : 10/557,694
Filed : November 22, 2005

22. (Canceled)

23. (Canceled)

24. (Canceled)